## MAINTENANCE MANUAL

MONOSTORE V/PLANAR
PDP-8 Add-In
Semiconductor Memory System

MSC P/N 303-0112-000



# MONOSTORE V/PLANAR PDP-8 Add-In

## SEMICONDUCTOR MEMORY SYSTEM

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#### MAINTENANCE MANUAL

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MSC P/N 303-0112-000

Information contained in this manual is disclosed in confidence and may not be duplicated in full or in part by any person without prior written approval of Monolithic Systems Corporation. Its sole purpose is to provide the user with adequately detailed documentation so as to efficiently install, operate, maintain, and order spare parts for the system supplied. The use of this document for all other purposes is specifically prohibited.

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## MONOSTORE V/PLANAR PDP-8 Add-In

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#### SECTION I

## GENERAL DESCRIPTION

## 1.1 INTRODUCTION

This manual provides information for installing, operating, and maintaining the MONOSTORE V/Planar PDP-8 add-in memory systems. The material is arranged in five sections as follows:

## Section I General Description

This section provides the scope, contents, and arrangement of the manual. A general description and a list of system specifications are also given.

## Section II Installation and Operation

Instructions are provided for unpacking, inspecting and installing the memory system.

## Section III Theory of Operation

An overall description of the memory system is provided along with a timing diagram to aid in understanding the system and to support troubleshooting.

## Section IV Maintenance and Troubleshooting

This section gives recommended general maintenance procedures and troubleshooting information for diagnosing and locating a malfunction.

## Section V Drawings

This section contains schematics, assembly, and parts list for the memory system.



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## 1.2 GENERAL DESCRIPTION

The MONOSTORE V/Planar PDP-8 Add-In Memory System, P/N 303-0112-000, consists of a single planar 8Kxl2 memory assembly. All electronics and semiconductor static N-channel memory storage elements are contained on a single printed circuit board.

All signal interface is made through the DEC OMNIBUS<sup>TM</sup> Assembly. Data interfacing is provided by 12 bidirectional data bits. Addressing any one of the 8192 words is provided by 13 binary address bits, together with command and control information to define the memory mode required.

The memory system uses the +5V power available on the OMNIBUS assembly.

The maximum capacity of the board is 8192 words by 12 bits. The system can also be configured in 1024 word increments from 1024 up to and including 8192 words.

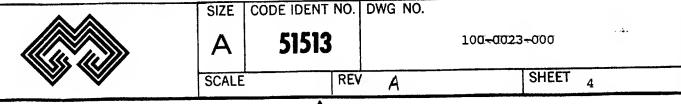
## 1.3 MODES OF OPERATION

	MD DIR L
Read Cycle - 1.2 $\mathcal{M}$ sec Transfers data from memory to the OMNIBUS.	1
Read/Write Cycle - 1.4 \( \times\) sec  Transfers data from memory to the  OMNIBUS during MD DIR L = 1 and  then writes data into memory from  the OMNIBUS during MD DIR L = 0.	1 → 0

## 1.4 SYSTEM SPECIFICATIONS

Characteristic	Specification
Storage Capacity	1024 words x 12 bits
	8192 words x 12 bits (1024 word increments)
Cycle Time	
Read	1.2 Msec
Read/Write	1.4 Msec

NOTE: DEC and OMNIBUS are trademarks of Digital Equipment Corporation.



1.4 System Specifications continued ..

<u>Characteristic</u> <u>Specification</u>

Read Access Time 600 nsec

Input Power +5V

Operating Environment
Temperature

0°C to +50°C

Relative Humidity 90% maximum without

condensation.

Physical Dimensions
Height 8.44 inches

Depth 0.5 inches Width 10.44 inches

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#### SECTION II

## INSTALLATION & OPERATION

## 2.1 INTRODUCTION

This section contains information for installation and operation of the memory system.

## 2.2 UNPACKING AND INSPECTION

Carefully remove the memory system from the shipping container. Remove any packing material from the assembly. Inspect the system for any damage or loose connections.

## 2.3 INSTALLING MEMORY SYSTEM

Remove the external top cover from the PDP-8 computer. Insert the memory system into the OMNIBUS Assembly. Reassemble the top cover. The memory system is now ready for use.

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## 2.4 I/O SIGNALS

	· · · · · · · · · · · · · · · · · · ·	<del> </del>	+	-			
Dl	D2	Cl	C2	B1	B2	Al	A2
TP	+15V	TP	+5V	TP	+5V	TP	+5V
TP	-15V	TP	-15V	TP	-15V	TP	-15V
GND	GND	GND	GND	GND	GND	SP GND*	GND
MA8L	IROL	I/O PAUSE L	тр1н	MA4L	INT STROBE L	MAOL	EMAOL
MA9L	IR1L	COL	ТР2Н	MA5L	BRK IN PROG L	MAlL	EMA1L
GND	GND	GND	GND	GND	GND	GND	GND
MA10L	IR2L	ClL	ТРЗН	MA6L	MA, MS LOAD CONT L	MA2L	EMA2L
MAllL	FL	C2L	ТР4Н	MA7L	OVERFLOW L	MA3L	MEM START L
MD8L	DL	BUS STROBE L	TS1L	MD4L	BREAK DATA CONT L	MDOL	MD DIR L
MD9L	EL	INTERNAL I/O L	TS2L	MD5L	BREAK CYCLE L	MD1L	SOURCE H
MD10L	USER MODE H	NOT LAST XFER L	TS3L	MD6L	LA ENABLE L	MD2L	STROBE H
GND	GND	GND	GND	GND	GND	GND	GND
MD11L	F SET L	INT ROST L	TS4L	MD7L	INT IN PROG H	MD3L	INHIBIT H
DATA 8L	PULSE LA H	INITIALIZE H	LINK DATA L	DATA 4L	RES 1 H	DATA OL	RETURN H
DATA 9L	STOP L	SKIP L	LINK LOAD L	DATA 5L	RES 2H	DATA 1L	WRITE H
GND	GND	GND	GND	GND	GND	GND	GND
DATA 10L	KEY CONTROL L	CPMA DISABLE L	IND 1L	DATA 6L	RUN L	DATA 2L	ROM ADDRESS L
DATA 11L	SW	MS, IR DISABLE L	IND 2L	DATA 7L	POWER OK H	DATA 3L	LINK L
	TP  TP  GND  MA8L  MA9L  GND  MA10L  MA11L  MD8L  MD9L  MD10L  GND  MD11L  DATA 8L  DATA 9L  GND  DATA 10L	TP +15V  TP -15V  GND GND  MA8L IROL  MA9L IRIL  GND GND  MA10L IR2L  MA11L FL  MD9L DL  MD9L EL  MD10L USER MODE H  GND GND  MD11L F SET L  DATA 8L PULSE LA H  DATA 9L STOP L  GND GND  DATA 10L KEY CONTROL L	TP +15V TP  TP -15V TP  GND GND GND  MA8L IROL I/O PAUSE L  MA9L IR1L COL  GND GND GND  MA10L IR2L C1L  MA11L FL C2L  MD8L DL STROBE L  MD9L EL INTERNAL I/O L  MD10L USER MODE H NOT LAST XFER L  GND GND GND  MD11L F SET L INT ROST L  DATA 8L PULSE LA H INITIALIZE H  DATA 9L STOP L SKIP L  GND GND GND  DATA 10L KEY CPMA CONTROL L DISABLE L  DATA 11L SW MS, IR	TP +15V TP +5V  TP -15V TP -15V  GND GND GND GND GND  MA8L IROL I/O PAUSE L TP1H  MA9L IRIL COL TP2H  GND GND GND GND  MA10L IR2L C1L TP3H  MA11L FL C2L TP4H  MD8L DL STROBE L TS1L  MD9L EL INTERNAL I/O L  MD10L USER MODE H NOT LAST XFER L  GND GND GND GND  MD11L F SET L INT ROST L TS4L  DATA 8L PULSE LA H INITIALIZE H LINK DATA L  GND GND GND GND GND  DATA 10L KEY CPMA GND IND 1L  DATA 11L SW MS, IR IND 2L	TP         +15V         TP         +5V         TP           TP         -15V         TP         -15V         TP           GND         GND         GND         GND         GND           MA8L         IROL         I/O PAUSE L         TP1H         MA4L           MA9L         IRIL         COL         TP2H         MA5L           GND         GND         GND         GND         GND           MA10L         IR2L         C1L         TP3H         MA6L           MA11L         FL         C2L         TP4H         MA7L           MD4L         DL         STROBE L         TS1L         MD4L           MD9L         EL         INTERNAL ISSL         TS2L         MD5L           MD1L         USER MODE H         NOT LAST XFER L         TS3L         MD6L           GND         GND         GND         GND         GND           MD1L         F SET L         INT ROST L         TS4L	TP +15V TP +5V TP +5V  TP -15V TP -15V TP -15V  GND GND GND GND GND GND GND  MA8L IROL I/O PAUSE L TP1H MA4L STROBE L  MA9L IRL COL TP2H MA5L BRK IN PROG L  GND GND GND GND GND GND GND  MA10L IR2L C1L TP3H MA6L LOAD CONT L  MA11L FL C2L TP4H MA7L OVERFLOW L  MD8L DL STROBE L  MD9L EL INTERNAL TS2L MD5L BREAK CYCLE L  MD10L USER MODE H NOT LAST XFER L  GND GND GND GND GND GND GND  MD11L F SET L INT ROST L TS4L MD7L TNT IN PROG H  DATA 8L PULSE LA H INITIALIZE H LINK DATA L DATA RES 1 H  GND GND GND GND GND GND GND GND  DATA 10L KEY COMPA IND 1L DATA RES 2H  GND GND GND GND GND GND GND  DATA 10L KEY COMPA IND 1L DATA RUN L  DATA 10L KEY COMPA IND 1L DATA RUN L  DATA 10L KEY COMPA IND 1L DATA RUN L  GLATA 10L KEY COMPA IND 1L DATA RUN L  DATA 11L SW MS, IR IND 2L DATA POWER OK H	TP         +15V         TP         +5V         TP         +5V         TP           TP         −15V         TP         −15V         TP         −15V         TP           GND         GND         GND         GND         SP GND*           MA8L         IROL         I/O PAUSE L         TP1H         MA4L         INT STROBE L         MA0L           MA9L         IRIL         COL         TP2H         MA5L         PRGG L         MA1L           GND         GND         GND         GND         GND         GND         GND           MA1OL         IRIL         COL         TP3H         MA6L         MA7, MS         MA2L           MA1OL         IRIL         COL         TP3H         MA6L         MA7, MS         MA2L           MA1OL         IRIL         COL         TP4H         MA7L         OVERFLOW L         MA3L           MA1OL         IRIL         COL         TP4H         MA7L         OVERFLOW L         MA3L           MA1OL         IRIL         COL         TP4H         MA7L         OVERFLOW L         MA3L           MA1OL         IRIL         MA7L         MA7L         MA7L         MA3L         MA3L </td



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## SECTION III

## THEORY OF OPERATION

## 3.1 INTRODUCTION

This section describes the overall organization and operation of the MONOSTORE V/Planar PDP-8 Add-in Semiconductor Memory System. The system has a maximum capacity of 8192 words of 12 bits.

This section is organized into the following major parts:

Description	Paragraph
Memory Location Programming	3.2
Address Channel	3.3
Data Channel	3,4
Timing Circuitry	3.5

## 3.2 MEMORY LOCATION PROGRAMMING

The memory location is programmed via wire jumpers on the board. The user can program the memory to any location according to the following table:

STARTING	O=HI LEVEL EMA			1	x8K GRAM	BOARD	MOD PRO	EN GRAM	
ADDRESS	0	1	2	/c	D	CAPACITY	A	В∖	
OK	0	0	0	/ <b>E</b>	F	4K 8K	1	A 2	
4K	0	0	1	F	E	4K 8K	2 2	A 3	
> 8K	0	1	0	E	F	4K 8K	3	A 4	
12K	0	1	1	F	E	4K 8K	4	A 5	
× 16ĸ	1	0	0	E	(F)	4ĸ 8ĸ	5 (5)	A 6	
20K	1	0	1	F	E	4K 8K	6 6	A 7	
24K	1	1	0	Е	F	4K 8K	7 7	A 8	
28K	1	1	1	F	E	4K <del>-</del>	8 -	A -	



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Jumpers at

## 3.2 Memory Location Programming continued ...

The computer generated addresses EMAO, EMA1, and EMA2 are decoded in blocks of 4K with a maximum of two 4K blocks of memory on a single board. If the generated addresses are within the programmed range a memory cycle will be initiated by MEM START L. This circuitry is shown on Sheet 1 of the schematic.

#### 3.3 ADDRESS CHANNEL

When a memory cycle is initiated the information on the address lines MAOL -> MAILL is used as follows:

 $ext{MA2L} o ext{MAllL}$  - These address bits are buffered in order to drive the complete memory array.

MAOL, MAIL - These address bits are decoded in conjunction with EMA2 to generate the lK, 2K...8K cenable pulses required by the memory elements. The cenable pulse then enables only one row of memory elements at any one time thereby preventing interaction of data bits.

The address channel and cenable circuits are shown on Sheet 1 of the schematic.

#### 3.4 DATA CHANNEL

When a memory cycle, READ, is initiated, the information previously stored in the memory elements is accessed and transmitted onto the MDOL  $\rightarrow$  MDIL lines for use by the computer for as long as MD DIR L = 1.

When a memory cycle, READ/WRITE, is initiated the READ cycle is repeated until MD DIR L = 0. At that time the WRITE phase of the memory cycle is performed and the information on the MDOL  $\rightarrow$  MDILL lines is buffered and stored in the memory elements at the same address as the first phase READ portion of the cycle.

The data channel circuit is shown on Sheet 2 of the schematic.

## 3.5 TIMING CIRCUITRY

All internal and I/O pulses or signals, except the storage element "write" pulse, are generated from timing pulses TS1L  $\rightarrow$  TS4L, TP1H  $\rightarrow$  TP3H, received at the OMNIBUS interface.

The MEM START L signal is received by the memory system and generates a READ or READ/WRITE cycle depending upon whether MD DIR L is a "1" or "1/0" respectively.

The timing pulses and signals at the OMNIBUS interface are generated according to the following timing diagram. The miscellaneous timing and control circuitry is shown on Sheets 1 and 2 of the schematic.

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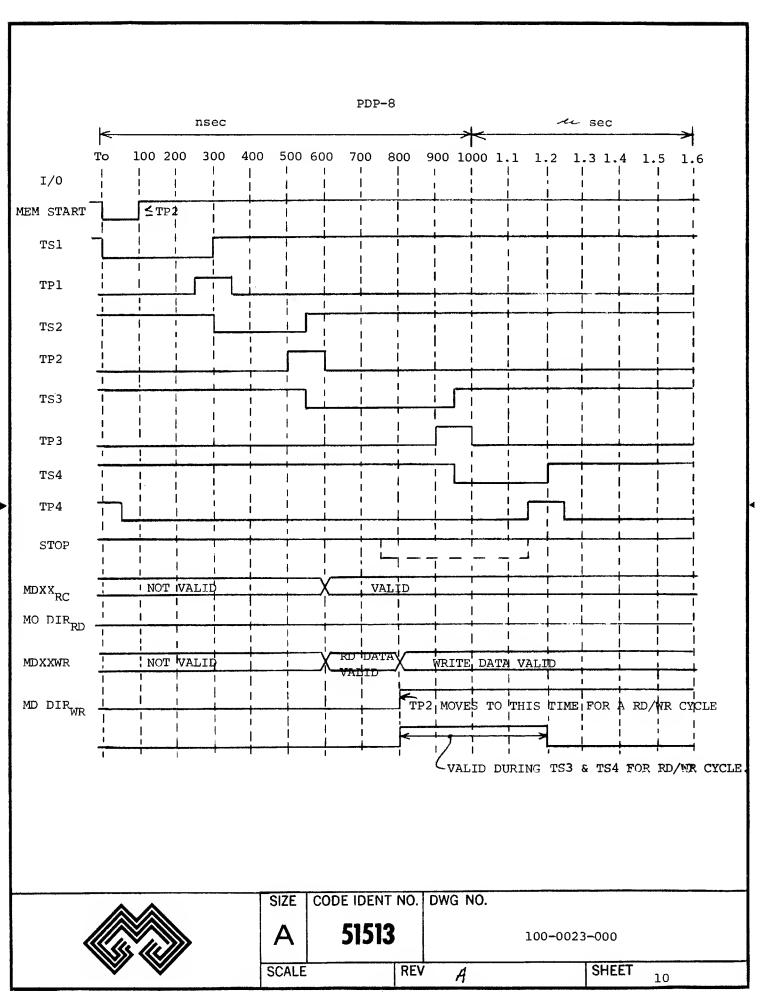
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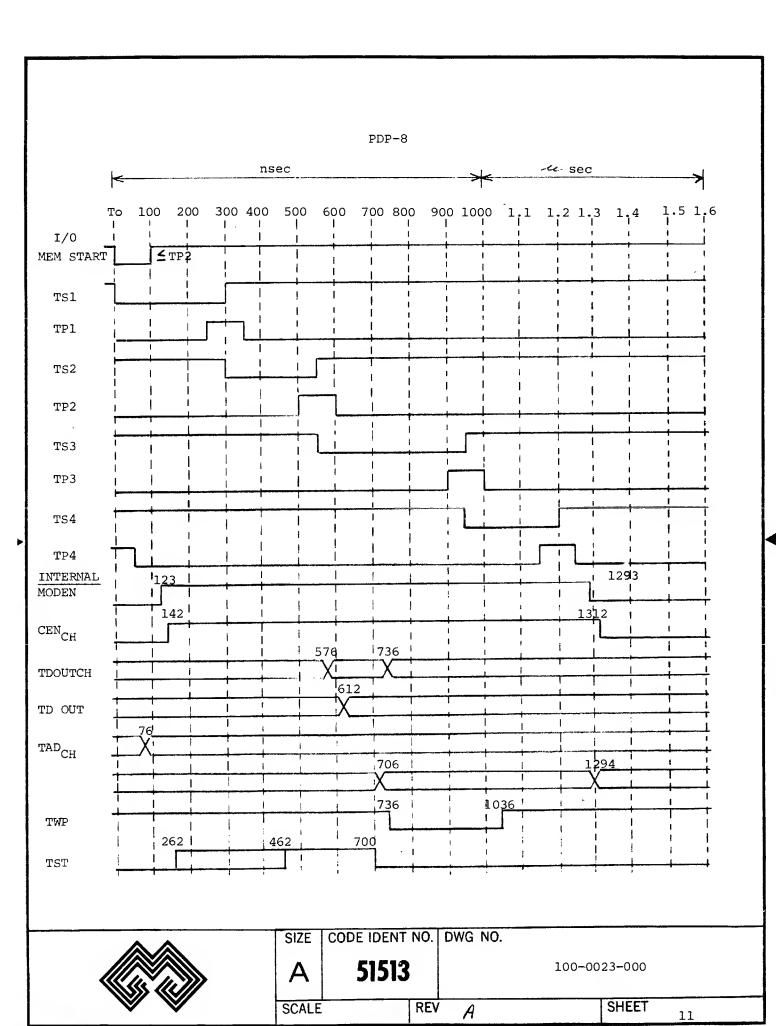
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#### SECTION IV

#### MAINTENANCE AND TROUBLESHOOTING

## 4.1 INTRODUCTION

This section presents troubleshooting instructions for ease of trouble location. Further localization of the trouble is to be found by means of the maintenance drawings in Section V. The theory of operation in Section III should be read and understood, along with a detailed review of the schematics in Section V in order to make effective use of this section.

## 4.2 PREVENTIVE MAINTENANCE

## 4.2.1 Visual Inspection

This inspection includes checking for loose programming wires, components, and discoloration of parts. The inspection should be performed with a minimum of prying or moving of parts.

## 4.2.2 Cleaning

Cleaning should be limited to removal of excess dust or particles. Never use any abrasive on any part of the gold fingers on the edge connectors. Low pressure compressed air can be used for removing dust or dirt and an aerosol cleaner can be used, with light brushing, to do the gold contacts.

## 4.2.3 DC Voltages

The +5V DC voltage should be maintained at:

+5V <u>+</u> 5%

## 4.3 TROUBLESHOOTING

To facilitate troubleshooting the following information, cause and effect, can be used to isolate the proglem to a particular area. From there on the schematics should be used to determine the exact component that is at fault.

Effect

Cause

Single bit failure, all addresses.

Data receiver/driver/read register

Complete word failure, all addresses.

DC voltage/WR pulse/strobe pulse.



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4.3 Troubleshooting continued ...

Effect

Cause

Single bit failure, single address.

Memory element

Four bit failure, all addresses

Read register/read data I/O driver.

Complete word failure, a 1K section.

CENABLE driver/CEN programming jumpers/address circuit for MAOL and

MAlL.

Complete or major part of word failure, all addresses

Address receiver/address buffer.

Non-retention of data.

DC voltage.

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## SECTION V

DRAWINGS

PARTS LIST

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ASSEMBLY

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SCHEMATIC

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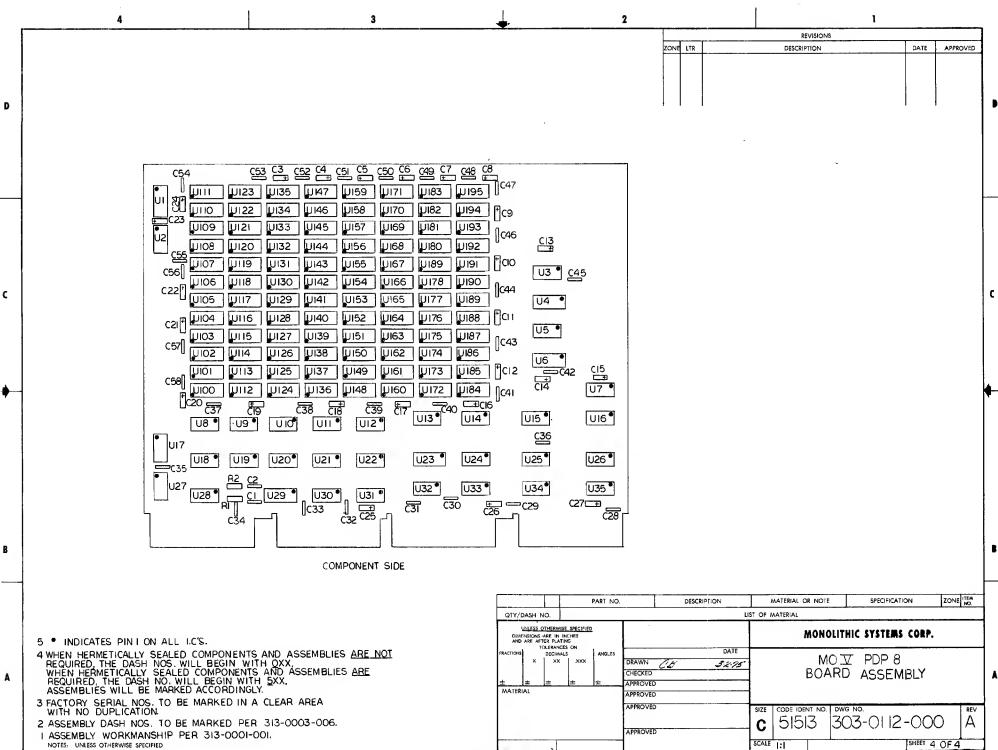
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							2							
		3	3	210-0003-10	I.C. SN7475	Ul, 4 6	3_							
		3	3	210-0002-31	I.C. SN7408	U2, 3 5	4							
₹		6	6	210-0002-02	I.C. SN74H04	U7, 9, 10, 12, 13, 18	5							
		10	10	210-0015-01	I.C. SP380	U8,15,22,24,25,26,27,28,30,35	6_							
A SIS		. 3	3	210-0002-05	I.C. SN74H00	Ull, 31, 32	7							
m	_	3	3	210-0002-08	I.C. SN74H10	U14, 19, 21	8							
CODE		2	2	210-0002-33	I.C. SN74H08	U16, 20	9							
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PL DWG	-	]	1	210-0006-02	I.C. SN74123	U29	12							
NG NO.							13							
		_	96	210-0028-002	Array 2102-1	U100-U195	14							
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303-01							16							
12		-		,			17							
2-000		25	25	201-0018-01	C 6 9 F 107	C3-C27	18							
1		3]			Cap. 6.8 F, 10V		19							
			31	701-0001-03	Cap1 F, 50V	C28-58								
		]	1		CAP 15pf	C1:	20							
1		]	1	201-0006-046	CAP 100pf	C2	21							

	QTY/D.	ASH NO		LIST OF MATERIAL								
		002	00]	PART NO.	DESCRIPTION	MATERIAL OR NOTE	SPECIFICATION	NO.				
		]	[1	214-0002-:026	RES. 11K 1/4W 5%	Rl,		23				
		]	1	214-0002-024	RES. 9.1K 1/4W 5%	R2		24				
		]4	14	208-0060-001	TERMINAL	1-8, A-F		25				
								26				
•		2	2	208-0057-001	CARD PULLS			27				
				,				28				
<u>~</u> <u>«</u>		4	4	208-0011-002	RIVETS			29				
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